

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	2095	"high voltage" and "low voltage" and "floating gate" and "control gate"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/07 17:49	
2	BRS	L2	1864	semiconductor and 1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/07 17:49	
3	BRS	L4	1658	gate and 3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/07 17:50	
4	BRS	L3	1658	@ad<=20011010 and 2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/07 17:51	